



100V 110mΩ N-Ch Power MOSFET

Features

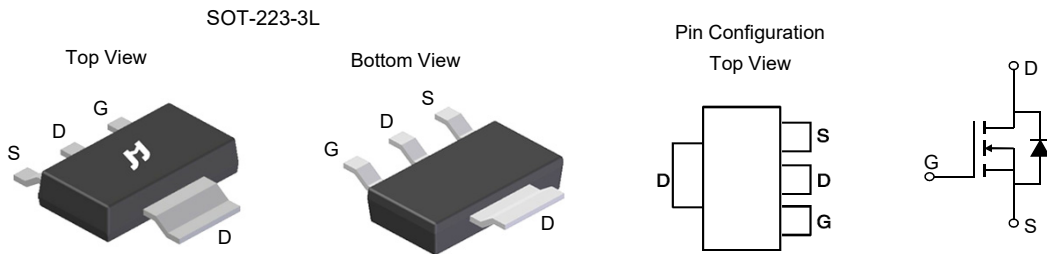
- Low Gate Charge
- Fast Switching
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Product Summary

| Parameter | Value | Unit |
|---|-------|------|
| V _{DS} | 100 | V |
| V _{GS(th)_Typ} | 1.9 | V |
| I _D (@ V _{GS} = 10V) ⁽¹⁾ | 5.9 | A |
| R _{DS(ON)_Typ} (@ V _{GS} = 10V) | 110 | mΩ |
| R _{DS(ON)_Typ} (@ V _{GS} = 4.5V) | 137 | mΩ |

Applications

- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

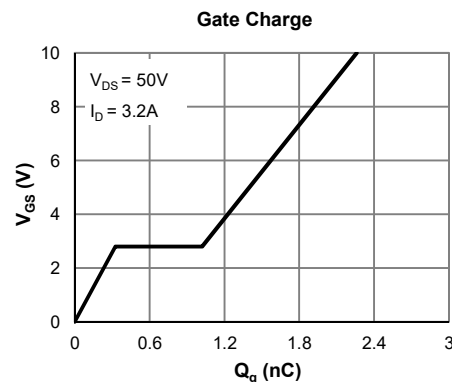
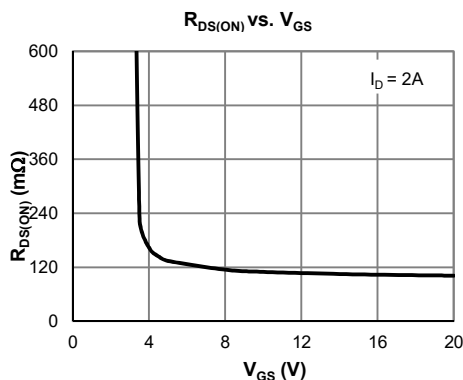


Ordering Information

| Device | Package | # of Pins | Marking | MSL | T _J (°C) | Media | Quantity (pcs) |
|----------------|------------|-----------|---------|-----|---------------------|--------------|----------------|
| JMSL10130AY-13 | SOT-223-3L | 3 | L10130A | 3 | -55 to 150 | 13-inch Reel | 4000 |

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---|-----------------------------------|------------------------|------|
| Drain-to-Source Voltage | V _{DS} | 100 | V |
| Gate-to-Source Voltage | V _{GS} | ±20 | V |
| Continuous Drain Current ⁽¹⁾ | I _D | T _C = 25°C | 5.9 |
| | | T _C = 100°C | 3.7 |
| Pulsed Drain Current ⁽²⁾ | I _{DM} | 24 | A |
| Avalanche Current ⁽³⁾ | I _{AS} | 4.3 | A |
| Avalanche Energy ⁽³⁾ | E _{AS} | 0.9 | mJ |
| Power Dissipation ⁽⁴⁾ | P _D | T _C = 25°C | 8.3 |
| | | T _C = 100°C | 3.3 |
| Junction & Storage Temperature Range | T _J , T _{STG} | -55 to 150 | °C |



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

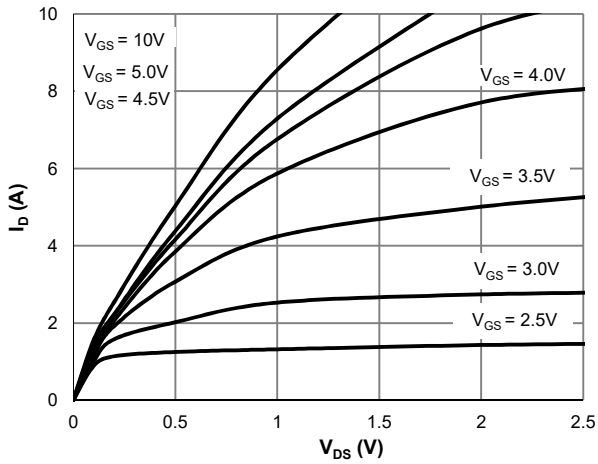
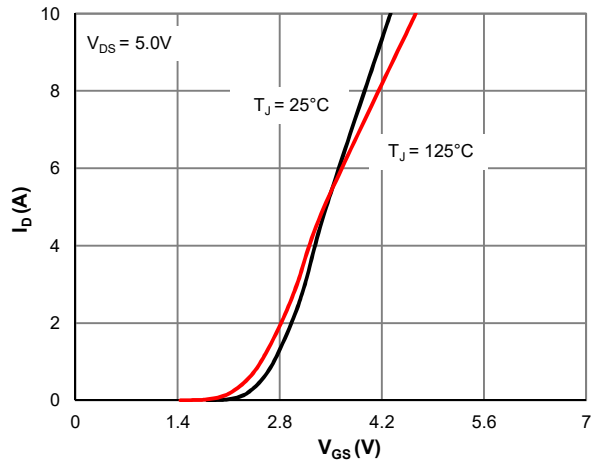
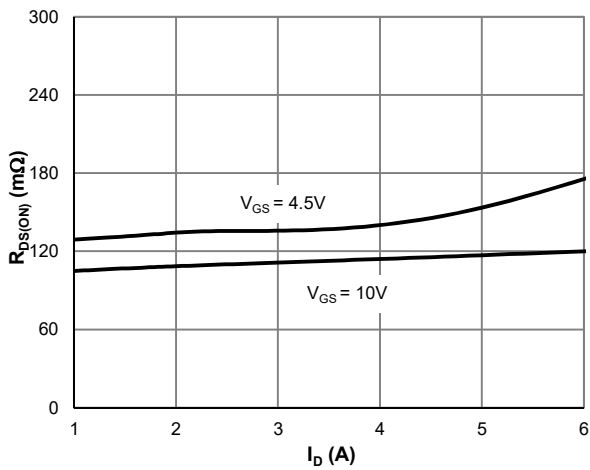
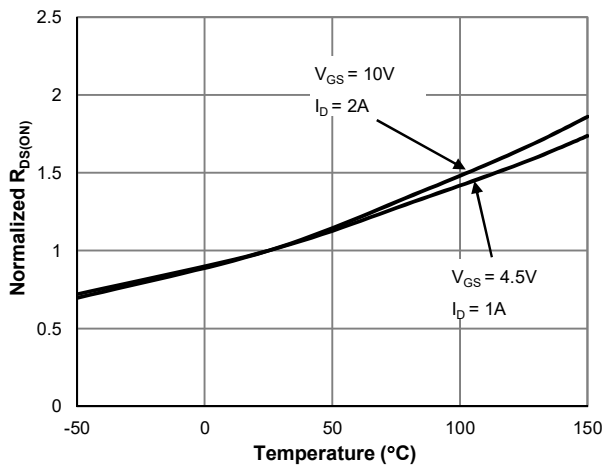
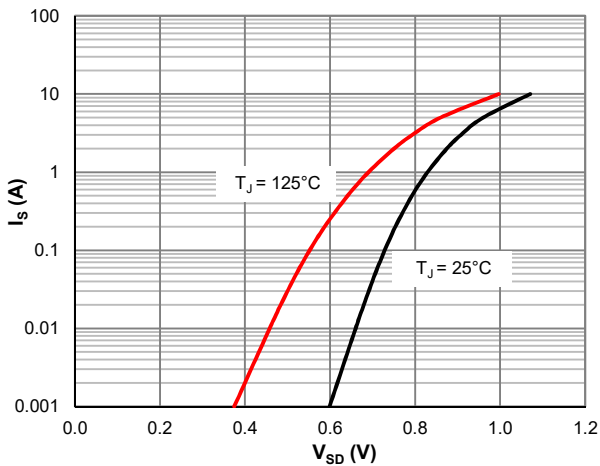
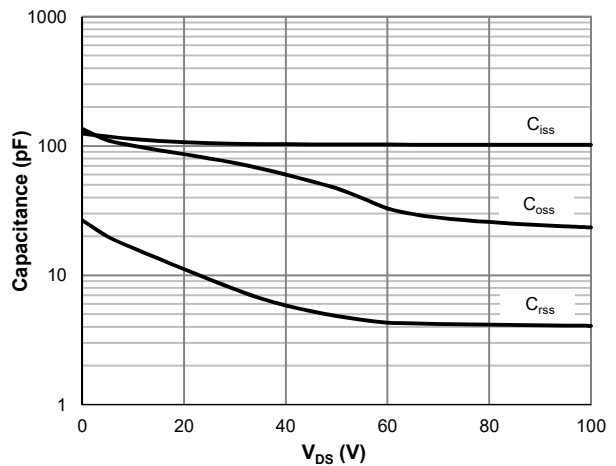
| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|---------------|---|---|------|------------|------------------|
| STATIC PARAMETERS | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ | 100 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$ | | | 1.0 5.0 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 1.2 | 1.9 | 3.0 | V |
| Static Drain-Source ON-Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{V}$, $I_D = 3.2\text{A}$ | | 110 | 138 | $\text{m}\Omega$ |
| | | $V_{GS} = 4.5\text{V}$, $I_D = 2.7\text{A}$ | | 137 | 180 | $\text{m}\Omega$ |
| Forward Transconductance | g_{FS} | $V_{DS} = 5\text{V}$, $I_D = 2\text{A}$ | | 4.1 | | S |
| Diode Forward Voltage | V_{SD} | $I_S = 1\text{A}$, $V_{GS} = 0\text{V}$ | | 0.70 | 1.0 | V |
| Diode Continuous Current | I_S | $T_C = 25^\circ\text{C}$ | | | 8 | A |
| DYNAMIC PARAMETERS ⁽⁵⁾ | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$ | | 103 | | pF |
| Output Capacitance | C_{oss} | | | 47 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 4.9 | | pF |
| Gate Resistance | R_g | $V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$ | | 2.6 | | Ω |
| SWITCHING PARAMETERS ⁽⁵⁾ | | | | | | |
| Total Gate Charge (@ $V_{GS} = 10\text{V}$) | Q_g | $V_{GS} = 0$ to 10V $V_{DS} = 50\text{V}$, $I_D = 3.2\text{A}$ | | 2.3 | | nC |
| Total Gate Charge (@ $V_{GS} = 4.5\text{V}$) | Q_g | | | 1.3 | | nC |
| Gate Source Charge | Q_{gs} | | | 0.3 | | nC |
| Gate Drain Charge | Q_{gd} | | | 0.7 | | nC |
| Turn-On Delay Time | $t_{D(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$ $R_L = 15.6\Omega$, $R_{GEN} = 6\Omega$ | | 2.1 | | ns |
| Turn-On Rise Time | t_r | | | 3.3 | | ns |
| Turn-Off Delay Time | $t_{D(off)}$ | | | 7.5 | | ns |
| Turn-Off Fall Time | t_f | | | 3.2 | | ns |
| Body Diode Reverse Recovery Time | t_{rr} | | $I_F = 3.2\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$ | | 21 | |
| Body Diode Reverse Recovery Charge | Q_{rr} | $I_F = 3.2\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$ | | 8.0 | | nC |

Thermal Performance

| Parameter | Symbol | Typ. | Max. | Unit |
|---|-----------------|------|------|---------------------------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 55 | 66 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 11.5 | 15.0 | $^\circ\text{C}/\text{W}$ |

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\mu\text{H}$, $V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

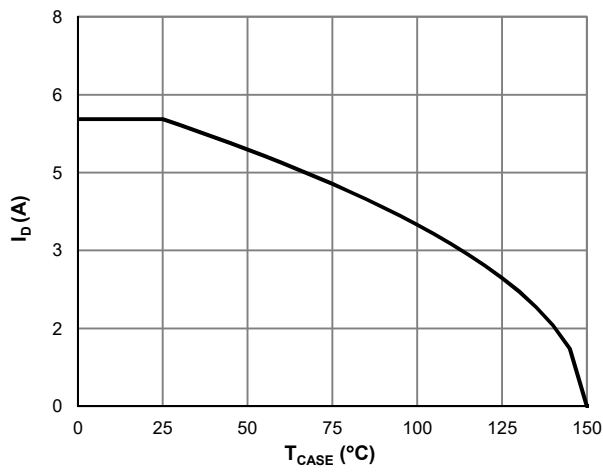


Figure 7: Current De-rating

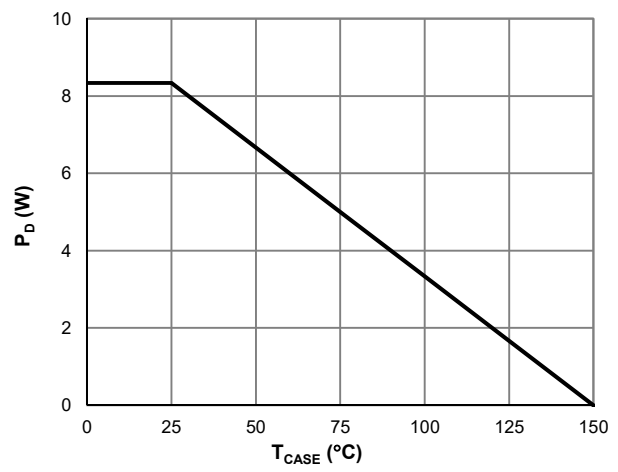


Figure 8: Power De-rating

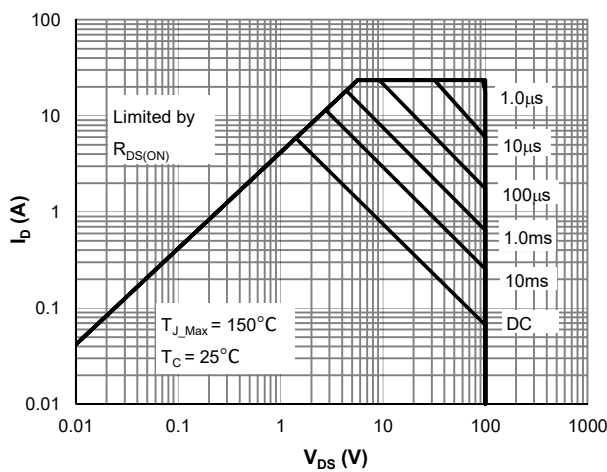


Figure 9: Maximum Safe Operating Area

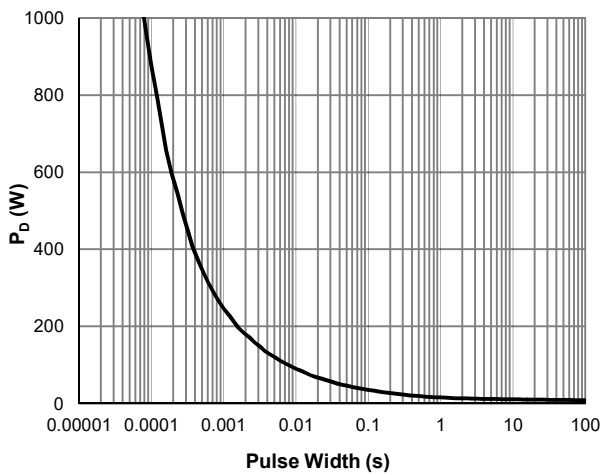


Figure 10: Single Pulse Power Rating, Junction-to-Case

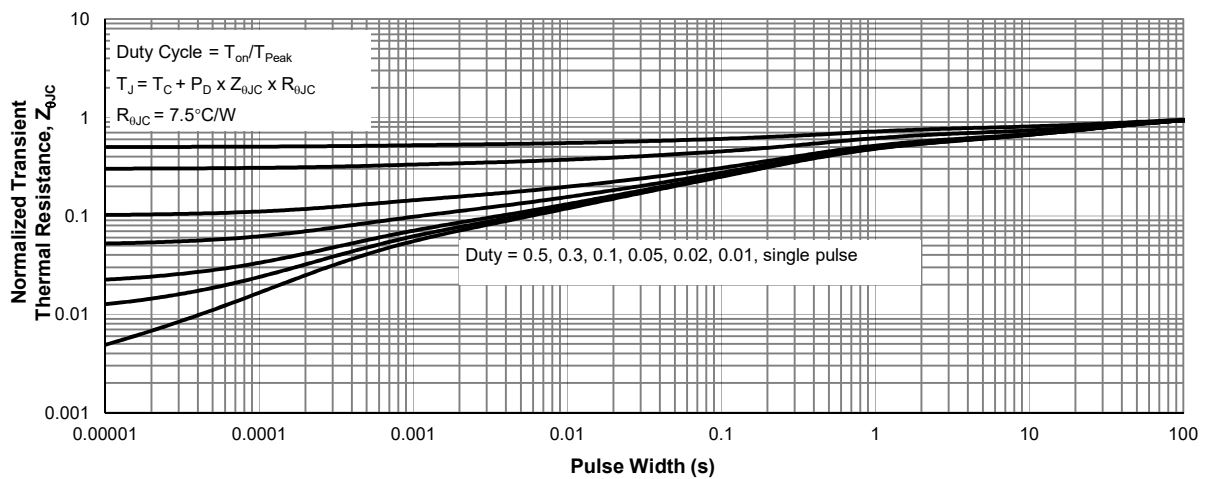
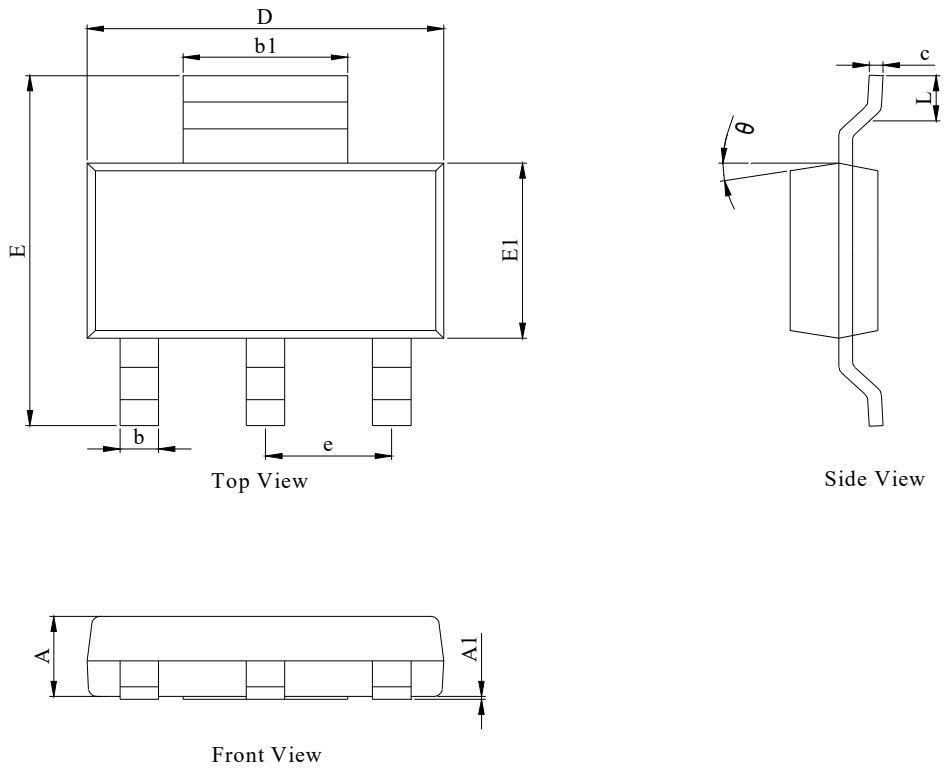


Figure 11: Normalized Maximum Transient Thermal Impedance

SOT-223-3L Package Information
Package Outline


| DIM. | MILLIMETER | | |
|----------|------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 1.50 | 1.60 | 1.80 |
| A1 | 0.01 | 0.06 | 0.10 |
| b | 0.60 | 0.70 | 0.80 |
| b1 | 2.90 | 3.00 | 3.10 |
| D | 6.30 | 6.50 | 6.70 |
| E | 6.70 | 7.00 | 7.30 |
| E1 | 3.30 | 3.50 | 3.70 |
| c | 0.22 | 0.26 | 0.32 |
| L | 0.70 | 0.90 | 1.10 |
| e | 2.30 BSC | | |
| θ | - | - | 10° |

Recommended Soldering Footprint
